



A high energy resolution gamma-ray TES calorimeter with 0.5 ms response time

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Applications & requirements

- Astrophysics

- ^{44}Ti (68.9/78.3 keV, $T_{1/2} \sim 59$ yr) γ -ray emission from supernova remnants

- direct information on the radioactive isotopes produced by the explosions
- not obscured by galactic dust

⇒ provides a stringent test of theories of supernova nuclear reactions.

Fly γ -ray calorimeters on balloons!

- Material analysis (EDXRD)

- γ -ray diffraction spectroscopy of crystals under ultra high pressure (\sim MPa) → **Poster by A. Hoshino**

- interesting structures \sim 80keV

- time evolution ⇒ fast response time

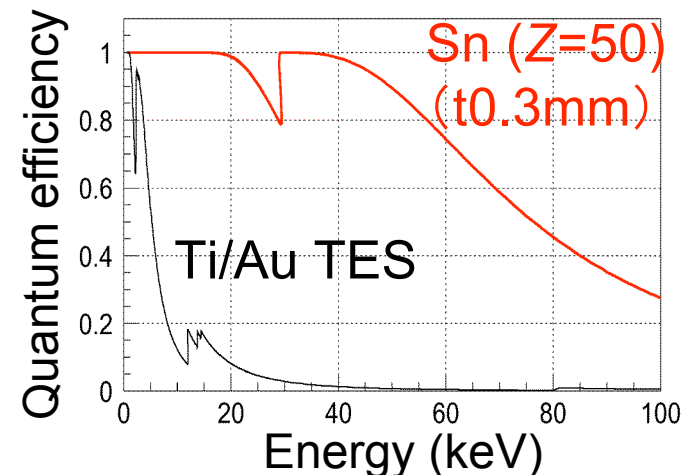
- Our GOAL

- Bandwidth \sim 100 keV

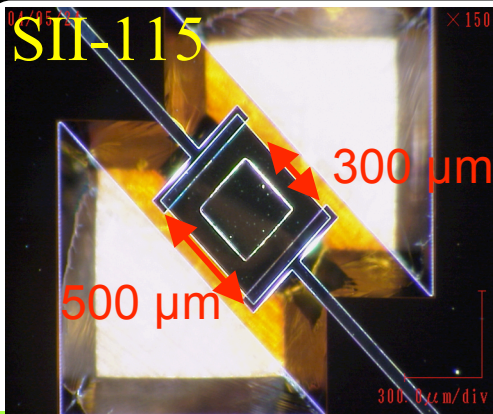
- Energy resolution $\Delta E \sim$ a few times 10 eV

- Fast response time $\tau \ll 1$ ms

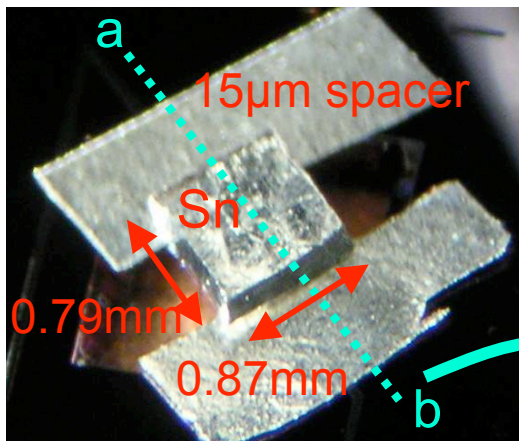
- High Efficiency @ \sim 80keV



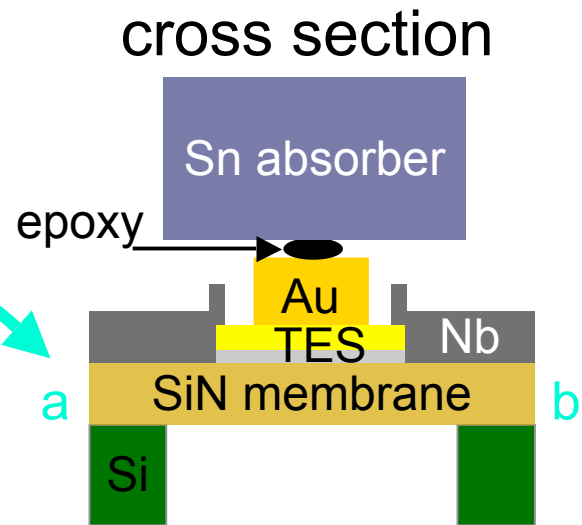
Our first trial (SII-115)



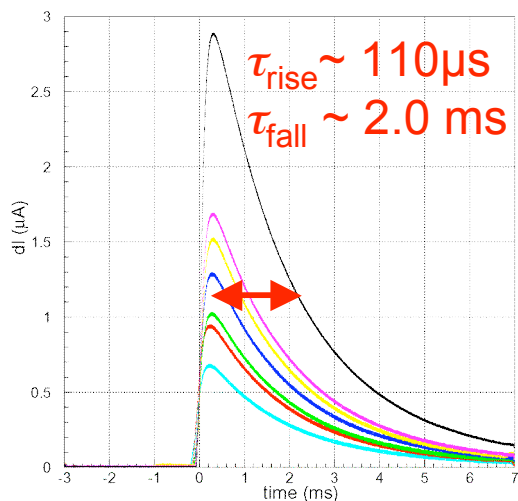
TES: Ti/Au(40/70nm)
 X-ray absorber: Au(500nm)
 Membrane: SiN bridge
 T_c : 151 mK



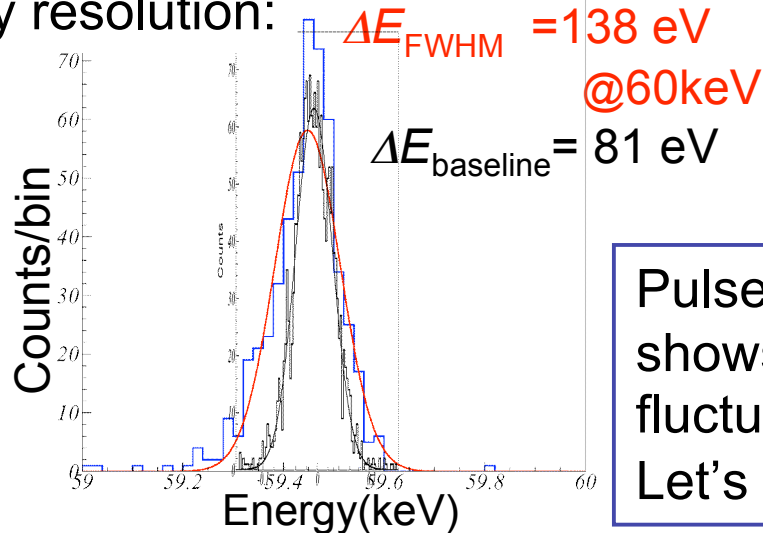
$C_a = 11.2$ pJ/K



Response:



Energy resolution:



Pulse shape analysis shows no significant fluctuation of τ_{rise} .
 Let's try a faster one!

Trade off

- Trade off between the signal loss and the position dependence.
 - $\tau_{fall} \downarrow (\cong G \uparrow) \Rightarrow \tau_{fall} / \tau_{rise} \downarrow \Rightarrow \Delta T_{TES} \downarrow \Rightarrow$ signal loss
 - $\tau_{rise} \downarrow (= G_a \uparrow) \Rightarrow$ Position dependence in the absorber \uparrow

- How fast can we make?

\Rightarrow SPICE simulation

- Boundary conditions:

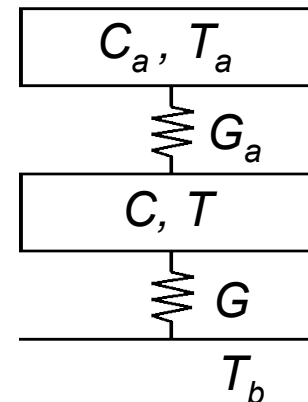
– Limited G_a : @150mK (@100mK)

- Stycast 2850FT $\sim 100\text{nW/K}$ (30nW/K) for $r = 100\mu\text{m}$, $h = 20\mu\text{m}$
- Kapitza $\sim 170\text{nW/K}$ (50nW/K) per $r = 100\mu\text{m}$ boundary (2 boundaries)
- electron-phonon $\sim 450\text{nW/K}$ (85nW/K)

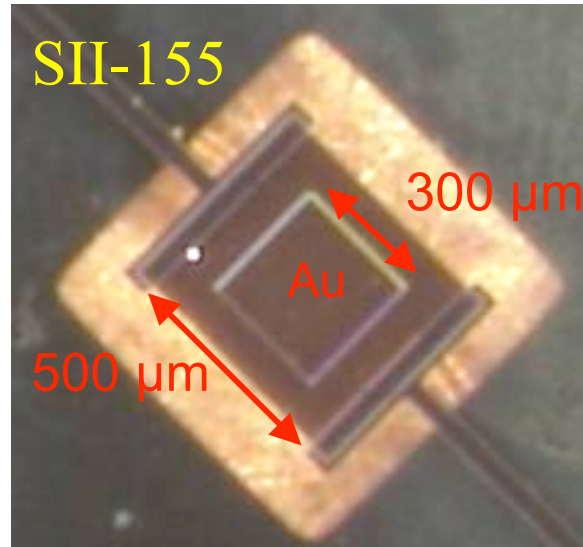
$\Rightarrow G_a \sim 50\text{nW/K}$ ($\sim 20\text{nW/K}$)

– Saturation at the transition edge:

- lower limit to C_a



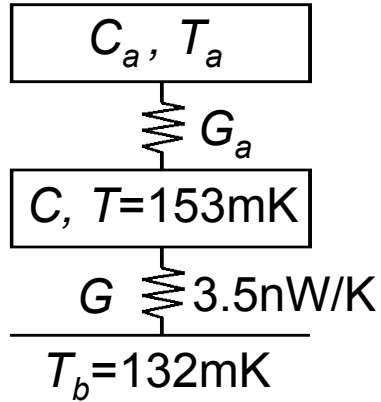
Our Second trial (SII-155)



TES: Ti/Au(40/120nm)
X-ray absorber: Au(500nm)
Membrane: SiN square
 T_c : 151 mK
 $C = 2.0$ pJ/K
 $G = 3.5$ nW/K
 $\Delta E = 12$ eV @ 5.9 keV

Saturation

Thermal model



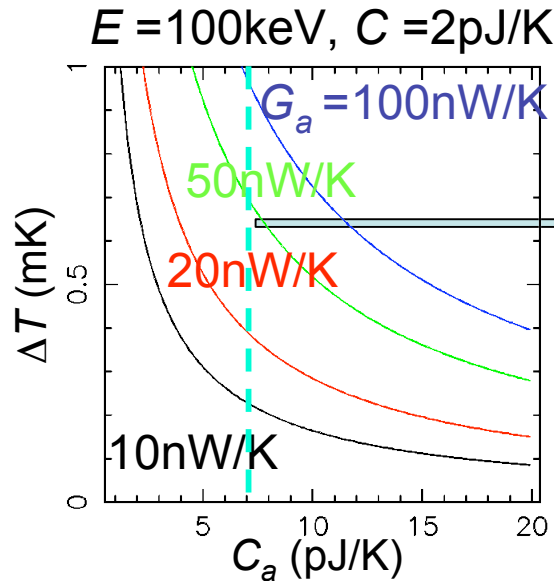
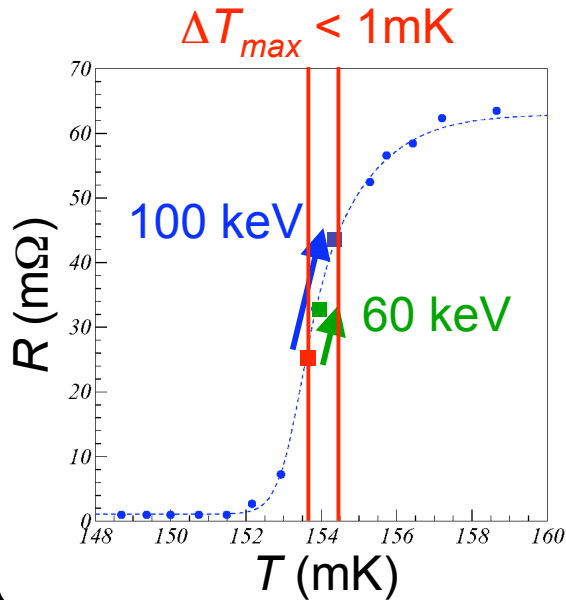
Temperature change of the TES

$$\tau_{\pm} = \frac{2\tau_0\tau_a}{\gamma\tau_0 + \mathcal{L}\tau_a \pm \sqrt{(\gamma\tau_0 + \mathcal{L}\tau_a)^2 - 4\tau_0\tau_a\mathcal{L}}}$$

$$\Delta T = \frac{E}{C_a} \frac{(\tau_a - \tau_+)(\tau_- - \tau_a)}{\tau_a(\tau_- - \tau_+)} \left(\exp\left(-\frac{t}{\tau_-}\right) - \exp\left(-\frac{t}{\tau_+}\right) \right)$$

$$t_{pk} = \frac{\ln(\tau_-/\tau_+)}{(1/\tau_+ - 1/\tau_-)}$$

$\tau_a \equiv C_a/G_a$ $\gamma \equiv 1 + C_a/C$
 $\tau_0 \equiv C/G$ $\mathcal{L} \equiv 1 + P\alpha/GT$
approx. $\alpha \sim (T/R)(\Delta R/\Delta T)$



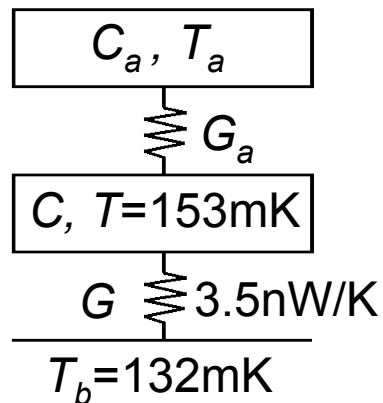
$C_a \sim 7\text{pJ/K}$

$(C > \alpha E_{max}/Tc = 21\text{pJ/K})$

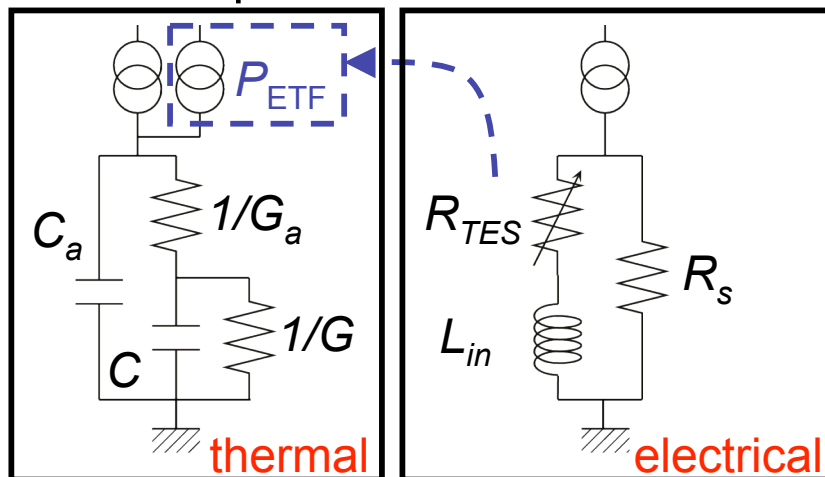
\Rightarrow size $\sim 700\mu\text{m}$

SPICE Simulation: Noise spectrum

Thermal model

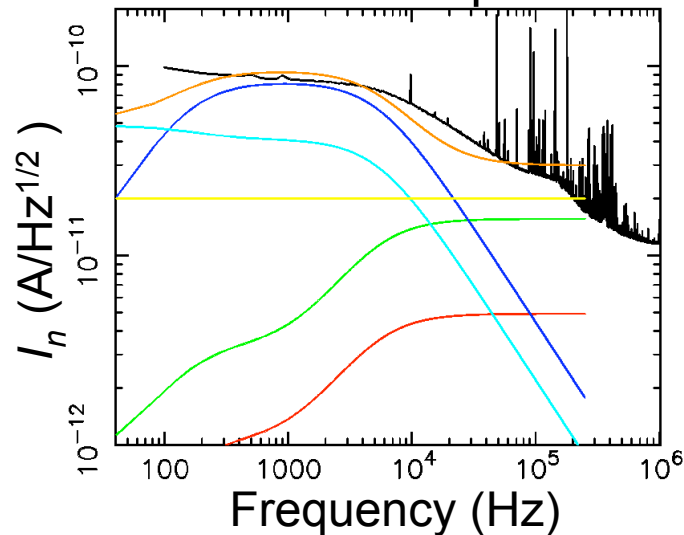


Equivalent circuit



(LLNL: Miyazaki et al.)

Current noise spectrum



Johnson noise of

– Shunt resistor $R_s = 3\text{m}\Omega$

– TES $R_{TES} = 25.58\text{m}\Omega$

Phonon noise at

– $G = 3.5\text{nW/K}$

– $G_a = 10\text{nW/K}$

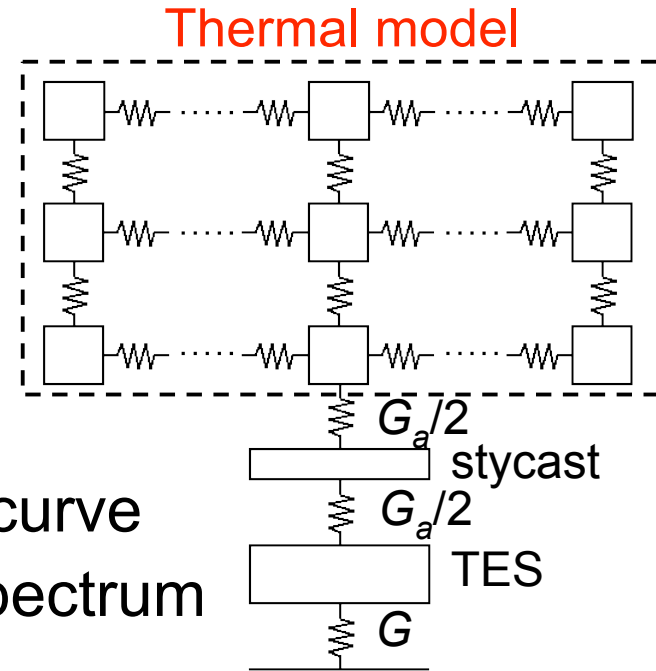
– Readout (SQUID) noise $20\text{pA}/\sqrt{\text{Hz}}$

– Total

SPICE Simulation: Position dependence (1)

- FEM-like model with SPICE

- Absorber: 3D network of C and G
7 x 7 x 3 elements
(Please imagine a 3D picture!)
- stycast: 1 element
- TES: 1 element



- generate pulses using a modeled R-T curve

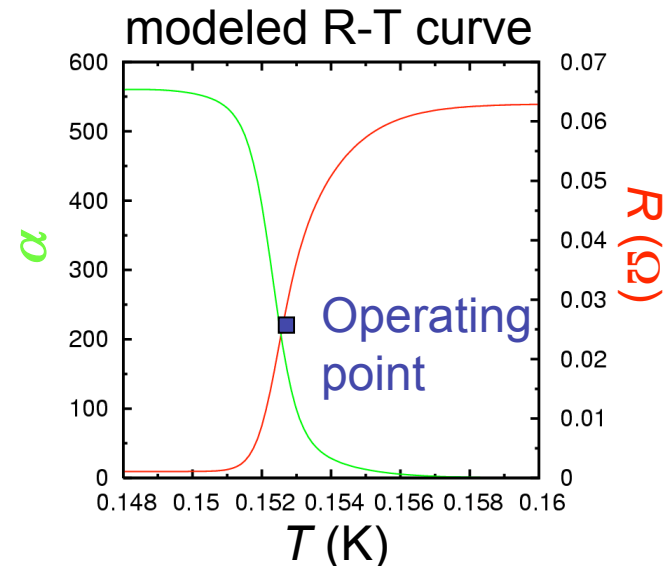
- optimal filtering with simulated noise spectrum

⇒ pulse height ⇒ ΔE_{FWHM}

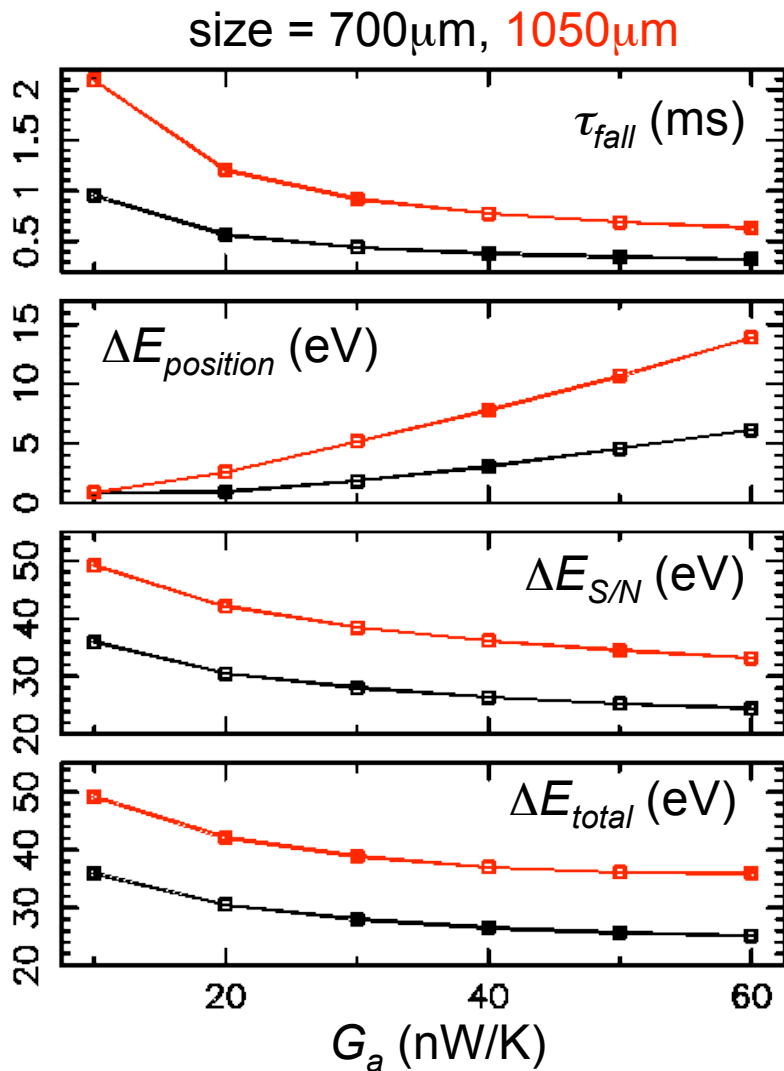
- Material Parameters of Sn:

- $\kappa_{Sn} = 1.24 T^{3.1} \text{ W/K/m}$ (foil)
- $c_{Sn} = 0.054 \text{ pJ/K}$

- Scan parameters: G_a , absorber area



SPICE Simulation: Position dependence (2)

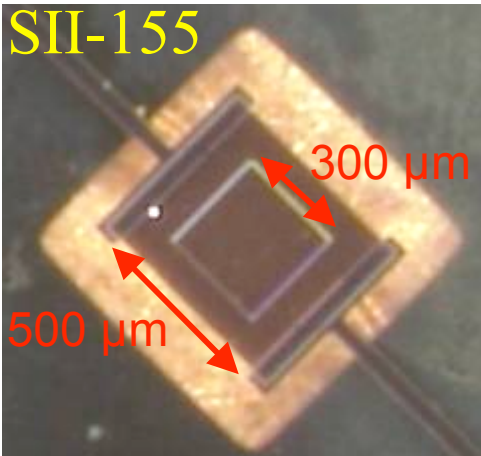


Make G_a as large as possible!

700 μm 25 eV && $\tau_{fall} = 300\mu\text{s}$
1050 μm 36 eV && $\tau_{fall} = 600\mu\text{s}$
achievable.

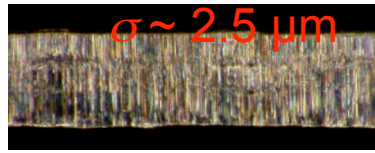
Our Second trial (SII-155)

SII-155

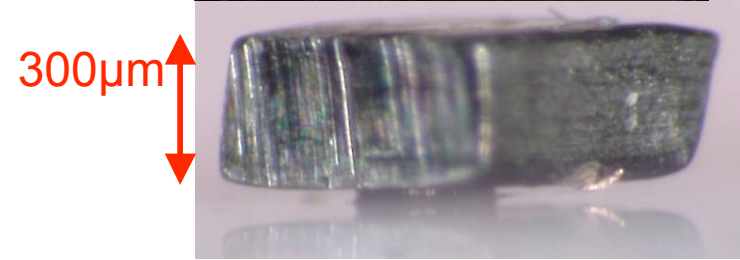
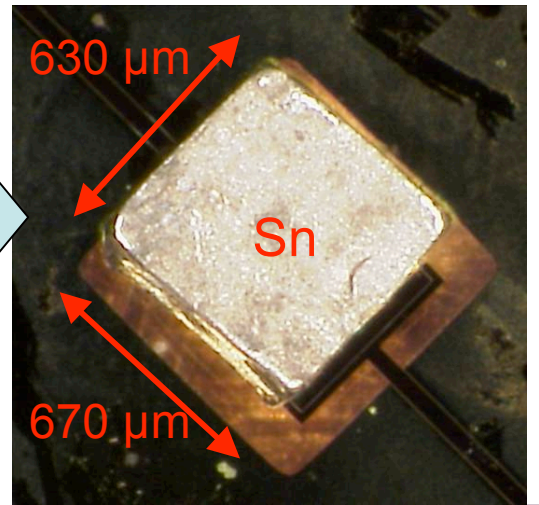
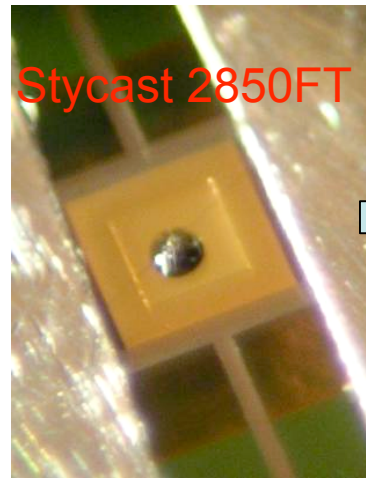
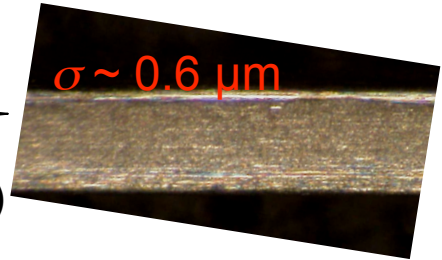


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 $\Delta E = 12$ eV @ 5.9 keV
 $C_a = 6.9$ pJ/K

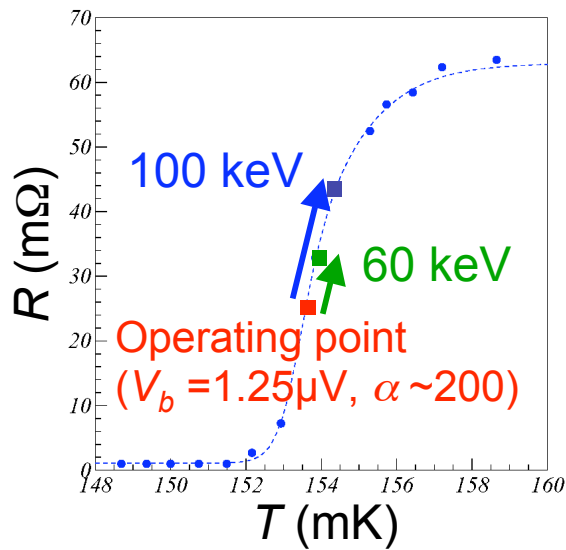
Surface roughness of Sn:



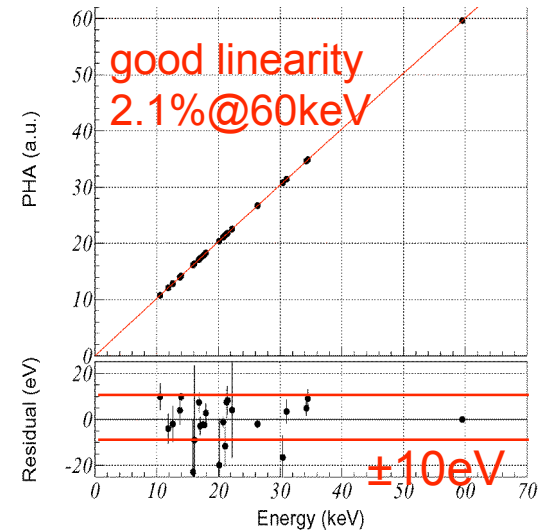
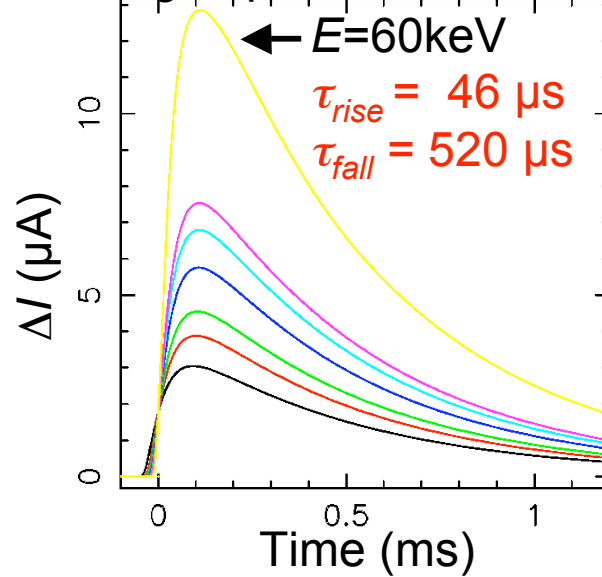
Polished
with alumina
powder(~ 3 μm)



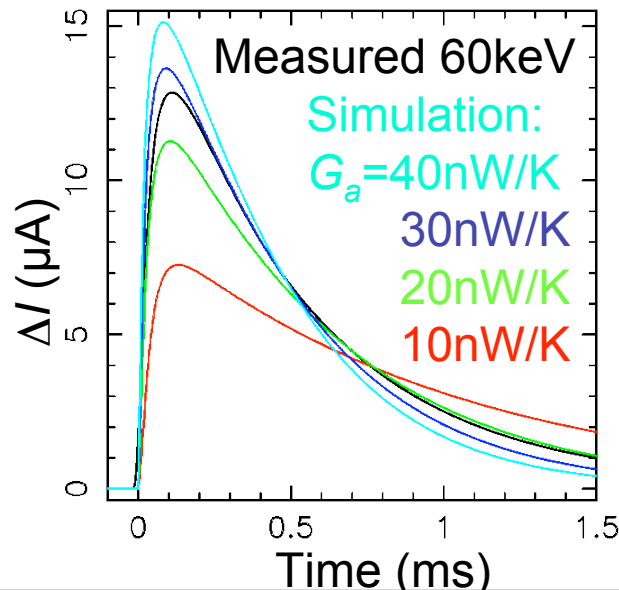
SII-155+Sn results (1)



averaged pulses of various E

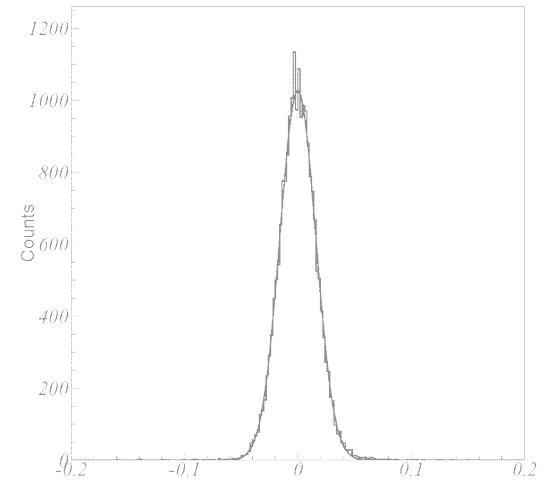
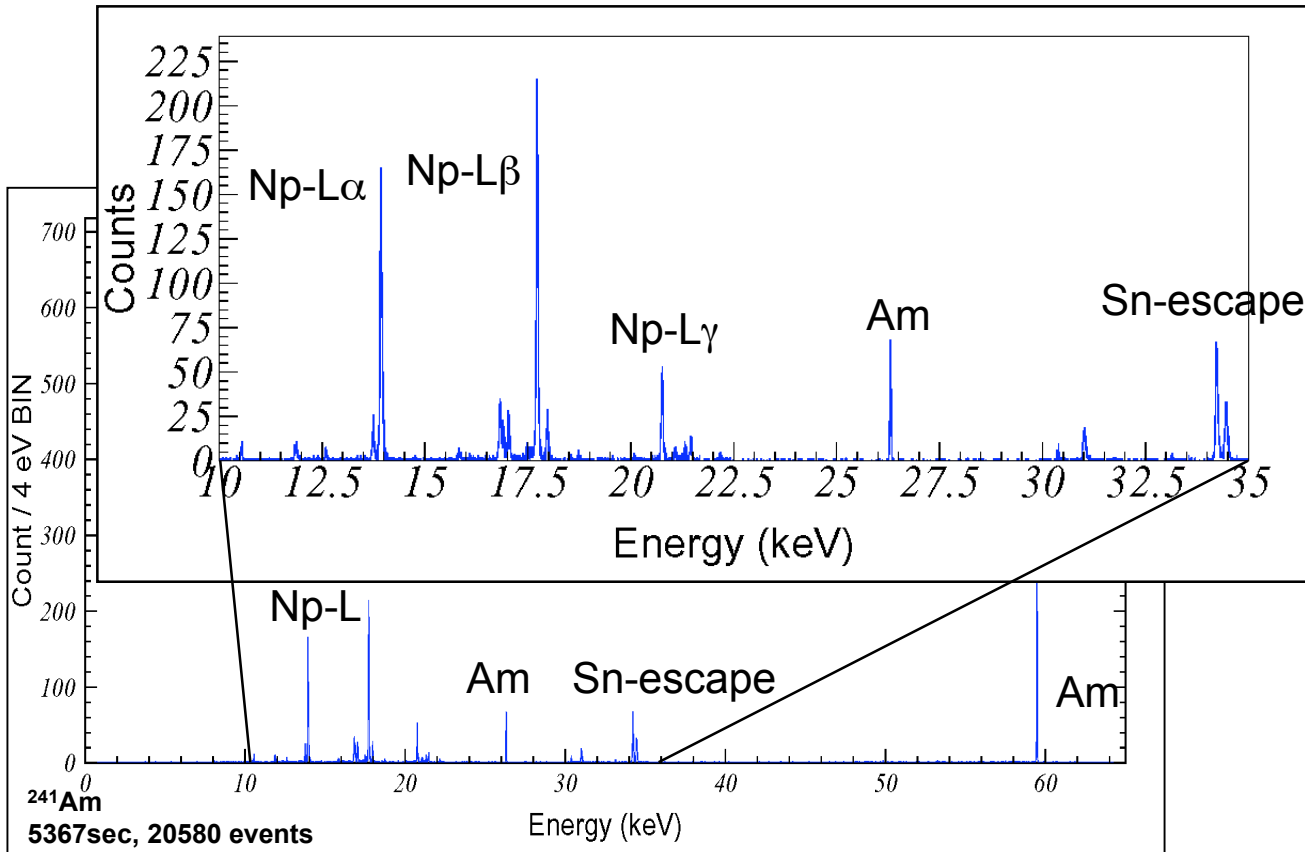


Comparison with
the SPICE simulation



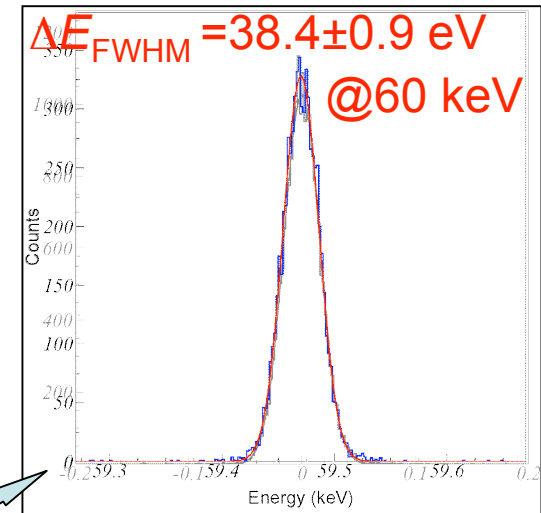
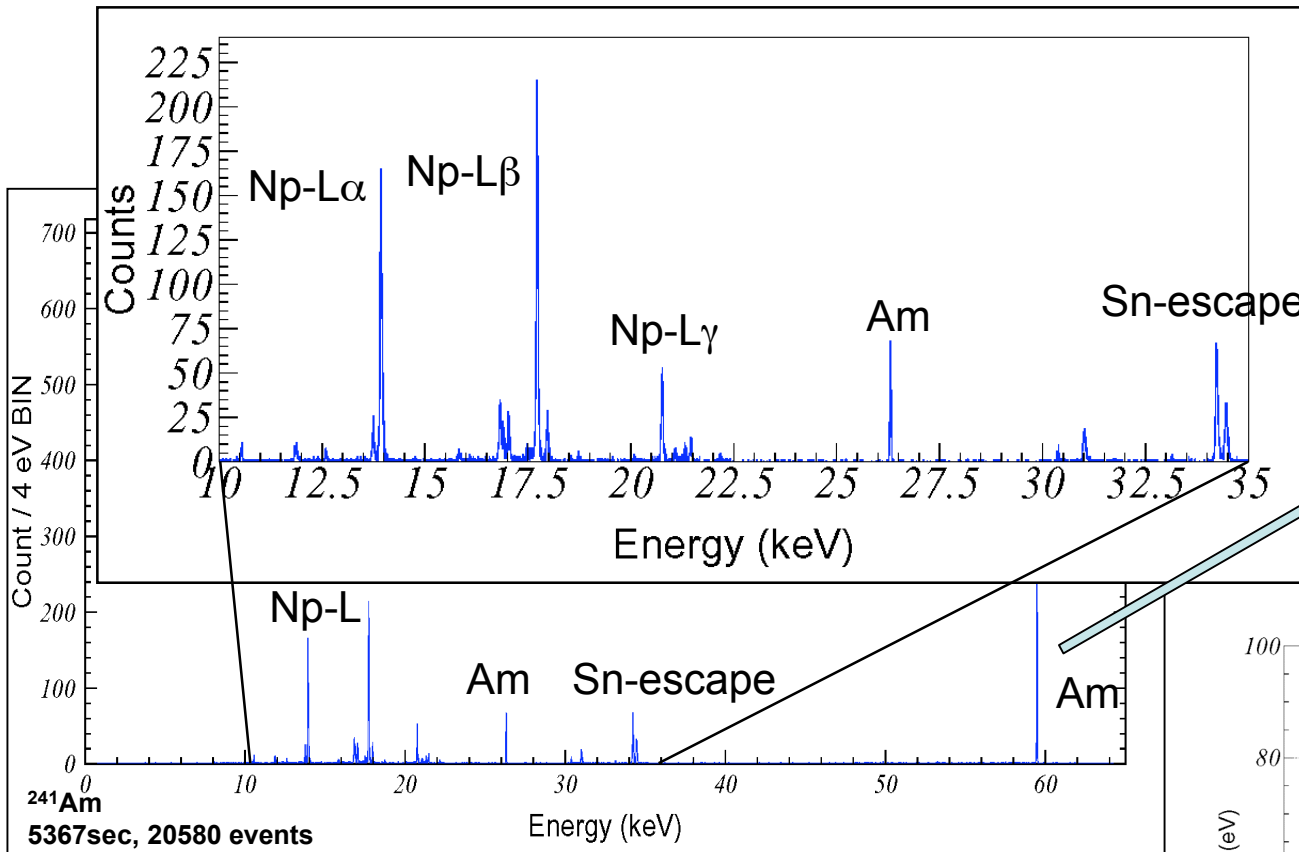
$G_a \sim 30 \text{ nW/K}$

SII-155+Sn results (2)

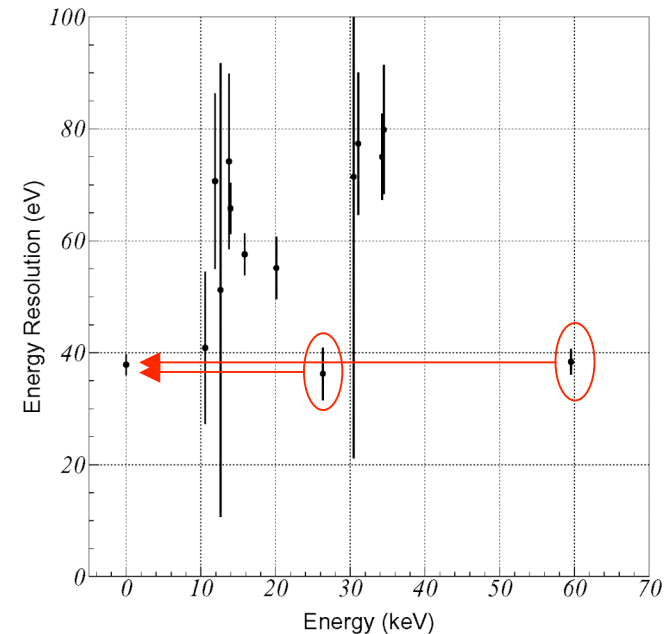


$$\Delta E_{\text{baseline}} = 37.9 \pm 0.7 \text{ eV}$$

SII-155+Sn results (2)

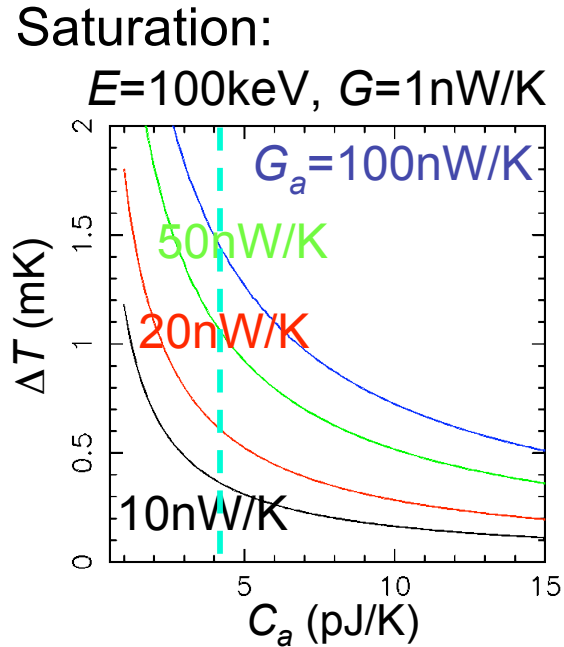
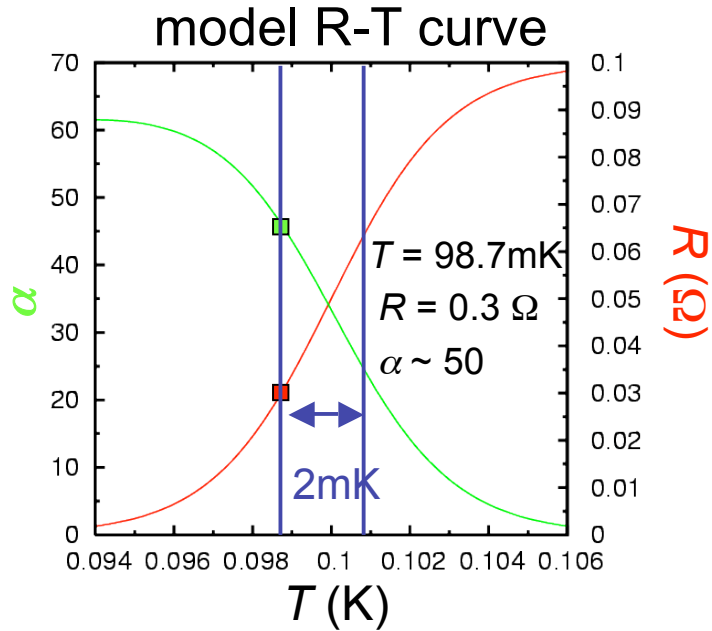


$\Delta E_{\text{baseline}} = 37.9 \pm 0.7 \text{ eV}$



Energy resolution of the nuclear γ -ray lines (26, 60 keV) agrees with $\Delta E_{\text{baseline}}$
 \Rightarrow no degradation by the position dependence

SPICE simulation: Ideal 100mK device



$C_a \sim 4\text{pJ/K}$
 \Rightarrow size $\sim 1000\mu\text{m}$

Results for $E=60\text{keV}$ signal

Scan parameters: $G_a = 10 - 50\text{nW/K}$, $G = 1 - 5\text{nW/K}$

Hard to list all. Results for some parameters are shown.

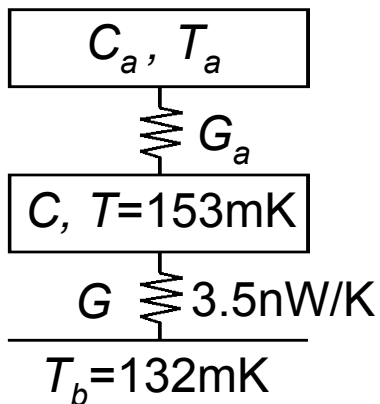
Size(μm)	G (nW/K)	G_a (nW/K)	τ_{fall} (μs)	$\Delta E_{S/N}$ (eV)	ΔE_{pos} (eV)	ΔE_{tot} (eV)
700	5	40	160	9.1	3.5	9.7
1050	3	40	420	10.8	6.8	12.7
1400	1	30	970	14.2	5.0	15.1

Summary

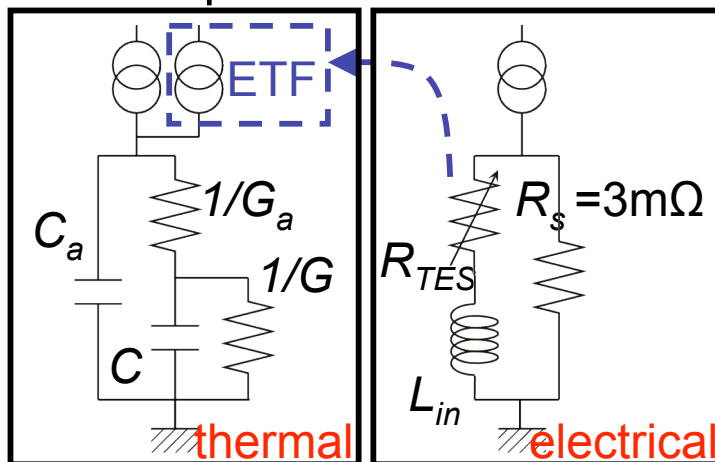
- Designed a fast response γ -ray TES calorimeter using SPICE simulation.
- 150mK device with $700\mu\text{m} \times 700\mu\text{m} \times 300\mu\text{m}$ tin absorber demonstrated
 - $\tau_{fall} = 520 \mu\text{s}$, $\tau_{rise} = 46\mu\text{s}$
 - $\Delta E = 38.4 \pm 0.9 \text{ eV}$ @60keV, $\Delta E_{baseline} = 37.9 \pm 0.7 \text{ eV}$
 - No degradation of ΔE due to the position dependence seen as the simulation tells.
- SPICE simulation for 100mK device shows
 - $\tau_{fall} < 500 \mu\text{s}$
 - $\Delta E < 15 \text{ eV}$is achievable with $1\text{mm}^2 \times 300\mu\text{m}$ absorber

SPICE Simulation: non-linearity

Thermal model



Equivalent circuit



- Generate simulated pulses using a modeled R-T curve
- Apply optimal filtering \Rightarrow pulse height

modeled R-T curve

